

What is claimed is:

1. A monocrystalline gallium nitride localized substrate comprising an area of grown monocrystalline gallium nitride locally on a monocrystalline silicon substrate.

2. A monocrystalline gallium nitride localized substrate according to Claim 1, wherein said monocrystalline gallium nitride is grown on silicon carbide formed on the monocrystalline silicon substrate.

3. A monocrystalline gallium nitride localized substrate according to any one of Claims 1 and 2, wherein said monocrystalline gallium nitride is grown by using silicon nitride as a mask.

4. A monocrystalline gallium nitride localized substrate according to any one of Claims 1 and 2, wherein said monocrystalline gallium nitride is grown by using silicon oxide as a mask.

5. A monocrystalline gallium nitride localized substrate according to any one of Claims 1 to 4, wherein said monocrystalline silicon substrate is an SOI substrate.

6. A method of manufacturing a monocrystalline gallium nitride localized substrate comprising the steps of:

forming silicon carbide on a monocrystalline silicon substrate; and

locally forming monocrystalline gallium nitride on said silicon carbide;

the method, wherein silicon nitride or silicon oxide is used as a mask in forming said monocrystalline gallium nitride.